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July 2015

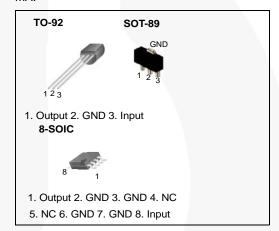
KA78LXXA / KA78L05AA 3-Terminal 0.1 A Positive Voltage Regulator

Features

- · Maximum Output Current of 100 mA
- Output Voltage of 5 V, 6 V, 8 V, 9 V, 10 V, 12 V, 15 V and 18 V
- Thermal Overload Protection
- · Short-Circuit Current Limiting
- Output Voltage Offered in ± 5% Tolerance

Description

The KA78LXXA / KA78L05AA series of fixed-voltage, monolithic, integrated circuit, voltage regulators are suitable for applications that require supply current up to 100 mA.



Ordering Information

Product Number	Package	Packing Method	Output Voltage Tolerance	Operating Temperature
KA78L05AZTA		Ammo		
KA78L05AZBU		Bulk		
KA78L06AZTA	•	Ammo		
KA78L08AZTA	•	Ammo		
KA78L09AZTA	TO-92	Ammo		
KA78L10AZTA		Ammo		
KA78L12AZTA		Ammo	± 5%	-40 to +125 °C
KA78L15AZTA		Ammo		
KA78L18AZTA	•	Ammo		
KA78L05AMTF		Tape & Reel		
KA78L08AMTF	SOT-89	Tape & Reel		
KA78L12AMTF	•	Tape & Reel		
KA78L05ADTF	8-SOIC	Tape & Reel		
KA78L05AAZTA	TO-92	Ammo	± 3%	0 to +125 °C

Block Diagram

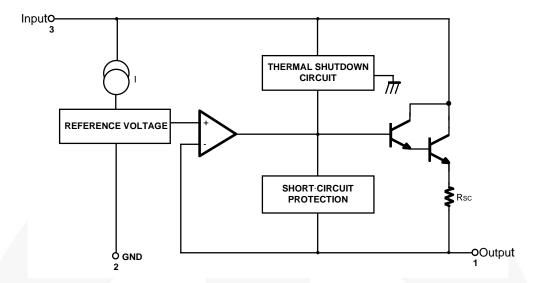


Figure 1. Block Diagram

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parar	meter	Value	Unit
V	Input Voltage	V _O = 5 V to 8 V	30	V
V _I	input voltage	V _O = 12 V to 18 V	35	V
т	Operating Temperature Bongs	KA78LXXA	-40 to +125	- °C
T _{OPR}	Operating Temperature Range	KA78L05AA	0 to +125	
T _{J(MAX)}	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-65 to +150	°C
$R_{\theta JC}$	Thermal Resistance, Junction-Case	TO-92	50	°C/W
		TO-92	150	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-Air	SOT-89	225	°C/W
		8-SOIC	160	°C/W

Electrical Characteristics (KA78L05A)

 $V_I = 10 \text{ V, } I_O = 40 \text{ mA, } -40^{\circ}C \leq T_J \leq 125^{\circ}C, \ C_I = 0.33 \ \mu\text{F, } C_O = 0.1 \ \mu\text{F, unless otherwise specified.}$

Symbol	Paramete	er	Cond	ditions	Min.	Тур.	Max.	Unit
Vo	Output Voltage		T _J = 25°C		4.8	5.0	5.2	V
ΔV_{O}	Line Regulation ⁽¹⁾		T _{.1} = 25°C	$7 \text{ V} \leq \text{V}_1 \leq 20 \text{ V}$		8	150	mV
ΔνΟ	Line Regulation V		1 j = 25 C	$8 \text{ V} \leq \text{V}_{\text{I}} \leq 20 \text{ V}$		6	100	mV
ΔV_{O}	Load Regulation (1)		T _{.I} = 25°C	$1 \text{ mA} \le I_{O} \le 100 \text{ mA}$		11	60	mV
7,0	Load Negulation V		1	1 mA \leq I _O \leq 40 mA		5.0	30	mV
Vo	Output Voltage		$7 \text{ V} \leq \text{V}_{\text{I}} \leq 20 \text{ V}$	1 mA \leq I _O \leq 40 mA			5.25	V
٧٥	Output Voltage		$7 \text{ V} \leq \text{V}_{\text{I}} \leq \text{V}_{\text{MAX}}^{(2)}$	1 mA \leq I _O \leq 70 mA	4.75		5.25	V
IQ	Quiescent Current		$T_J = 25^{\circ}C$			2.0	5.5	mA
ΔI_{Q}	Quiescent Current	With Line	8 V ≤V _I ≤ 20 V				1.5	mA
ΔI_{Q}	Change	With Load	$1 \text{ mA} \le I_O \le 40 \text{ mA}$	4			0.1	mA
V_N	Output Noise Voltag	е	$T_A = 25^{\circ}C, 10 \text{ Hz}$	≤ f ≤ 100 kHz		40		μV/Vo
$\Delta V_{O}/\Delta T$	Temperature Coefficient of V _O		$I_O = 5 \text{ mA}$			-0.65		mV/°C
RR	Ripple Rejection		$f = 120 \text{ Hz}, 8 \text{ V} \le 7$	$V_{I} \le 18 \text{ V}, T_{J} = 25^{\circ}\text{C}$	41	80		dB
V_{D}	Dropout Voltage		T _J = 25°C			1.7		V

- 1. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.
- 2. Power dissipation: $P_D \le 0.75 \text{ W}$.

Electrical Characteristics (KA78L06A)

 $V_I = 12 \text{ V, I}_O = 40 \text{ mA, -}40^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C, C}_I = 0.33 \text{ }\mu\text{F, C}_O = 0.1 \text{ }\mu\text{F, unless otherwise specified.}$

Symbol	Paramete	er	C	onditions	Min.	Тур.	Max.	Unit
Vo	Output Voltage		T _J = 25°C		5.75	6.00	6.25	V
41/	Line Regulation (3)		T _{.1} = 25°C	8.5 V ≤ V _I ≤ 20 V		64	175	mV
ΔV_{O}	Line Regulation V		1j = 25 C	9 V ≤ V _I ≤ 20 V		54	125	mV
41/	Load Regulation (3)		T - 25°C	1 mA ≤ I _O ≤ 100 mA		12.8	80.0	mV
ΔV_{O}	Load Regulation V		$T_J = 25^{\circ}C$	$1 \text{ mA} \le I_O \le 70 \text{ mA}$		5.8	40.0	mV
V	Output Voltage		$8.5 \text{ V} \le \text{V}_{\text{I}} \le 20 \text{ V}, 1 \text{ mA} \le \text{I}_{\text{O}} \le 40 \text{ mA}$				6.3	V
Vo	Output voltage		$8.5 \text{ V} \le \text{V}_{\text{I}} \le \text{V}_{\text{MAX}}^{(4)}, 1 \text{ mA} \le \text{I}_{\text{O}} \le 70 \text{ mA}$		5.7		6.3	V
1	Quiescent Current		T _J = 25°C				5.5	mA
lQ	Quiescent Current		T _J = 125°C			3.9	6.0	mA
ΔI_{Q}	Quiescent Current	With Line	9 V ≤ V _I ≤ 20 V	'			1.5	mA
ΔI_Q	Change	With Load	1 mA ≤ I _O ≤ 40	mA			0.1	mA
V _N	Output Noise Voltag	е	$T_A = 25^{\circ}C$, 10 Hz \leq f \leq 100 kHz			40		μV/Vo
$\Delta V_O/\Delta T$	Temperature Coeffic	cient of V _O	$I_O = 5 \text{ mA}$			0.75		mV/°C
RR	Ripple Rejection		$f = 120 \text{ Hz}, 10 \text{ V} \le \text{V}_{\text{I}} \le 20 \text{ V}, T_{\text{J}} = 25^{\circ}\text{C}$		40	46	7	dB
V_D	Dropout Voltage		T _J = 25°C			1.7		V

- 3. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.

 4. Power dissipation: P_D ≤ 0.75 W.

Electrical Characteristics (KA78L08A)

 $V_{I}=14~V,~I_{O}=40~mA,~-40^{\circ}C \leq T_{J} \leq 125^{\circ}C,~C_{I}=0.33~\mu F,~C_{O}=0.1~\mu F,~unless~otherwise~specified.$

Symbol	Parameter	Parameter		tions	Min.	Тур.	Max.	Unit
Vo	Output Voltage		T _J = 25°C		7.7	8.0	8.3	V
41/	Line Regulation (5	5)	T _{.l} = 25°C	$10.5 \text{ V} \le \text{V}_{\text{I}} \le 23 \text{ V}$		10	175	mV
ΔV_{O}	Line Regulation V	,	1 j = 25 C	11 V ≤ V _I ≤ 23 V		8	125	mV
41/	Load Regulation	(5)	T _{.l} = 25°C	$1 \text{ mA} \le I_{O} \le 100 \text{ mA}$		15	80	mV
ΔV_{O}	Load Regulation	,	1 _J = 25 C	$1 \text{ mA} \le I_{O} \le 40 \text{ mA}$		8	40	mV
V	Output Voltage		$10.5 \text{ V} \le \text{V}_{\text{I}} \le 23 \text{ V}$	$1 \text{ mA} \le I_O \le 40 \text{ mA}$	7.6		8.4	V
Vo	Output voitage		$10.5 \text{ V} \le \text{V}_{\text{I}} \le \text{V}_{\text{MAX}}^{(6)}$	$1~\text{mA} \leq I_O \leq 70~\text{mA}$	7.6		8.4	V
IQ	Quiescent Curren	it	T _J = 25°C			2.0	5.5	mA
ΔI_{Q}	Quiescent	With Line	11 V ≤ V _I ≤ 23 V				1.5	mA
ΔI_{Q}	Current Change	With Load	1 mA \leq I _O \leq 40 mA				0.1	mA
V _N	Output Noise Volt	tage	$T_A = 25^{\circ}C$, 10 Hz \leq f :	≤100 kHz		60		μV/Vo
$\Delta V_{O}/\Delta T$	Temperature Coefficient of V_O		I _O = 5 mA			-0.8		mV/°C
RR	Ripple Rejection		f = 120 Hz, 11 V ≤ V _I	≤ 21 V, T _J = 25°C	39	70		dB
V_D	Dropout Voltage		T _J = 25°C			1.7		V

- 5. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.

 6. Power dissipation: $P_D \le 0.75 \text{ W}$.

Electrical Characteristics (KA78L09A)

 $V_I = 15 \text{ V, } I_O = 40 \text{ mA, } -40^{\circ}C \leq T_J \leq 125^{\circ}C, \ C_I = 0.33 \ \mu\text{F, } C_O = 0.1 \ \mu\text{F, unless otherwise specified.}$

Symbol	Paramet	er	Condi	tions	Min.	Тур.	Max.	Unit
Vo	Output Voltage		T _J = 25°C		8.64	9.00	9.36	V
ΔV_{O}	Line Regulation (7)		T _{.l} = 25°C	$11.5 \text{ V} \le \text{V}_{\text{I}} \le 24 \text{ V}$		90	200	mV
740	Line Regulation V		1j = 25 C	13 V ≤ V _I ≤ 24 V		100	150	mV
ΔV_{O}	Load Regulation (7))	T _{.I} = 25°C	$1~\text{mA} \leq I_{O} \leq 100~\text{mA}$		20	90	mV
740	Load Regulation		1) = 23 0	$1 \text{ mA} \le I_{O} \le 40 \text{ mA}$		10	45	mV
Vo	Output Voltage		$11.5 \text{ V} \le \text{V}_{\text{I}} \le 24 \text{ V}$	$1~\text{mA} \leq I_{O} \leq 40~\text{mA}$	8.55		9.45	V
٧٥	Output Voltage		11.5 $V \le V_I \le V_{MAX}^{(8)}$	$1~\text{mA} \leq I_O \leq 70~\text{mA}$	8.55		9.45	V
IQ	Quiescent Current		$T_J = 25^{\circ}C$			2.1	6.0	mA
ΔI_{Q}	Quiescent Current	With Line	$13~V \leq V_I \leq 24~V$				1.5	mA
ΔI_{Q}	Change	With Load	1 mA \leq I _O \leq 40 mA				0.1	mA
V_N	Output Noise Volta	ge	$T_A = 25^{\circ}C, 10 \text{ Hz} \le f \le$	≤ 100 kHz		70		μV/Vo
$\Delta V_{O}/\Delta T$	Temperature Coefficient of V _O		$I_O = 5 \text{ mA}$			-0.9		mV/°C
RR	Ripple Rejection		$f = 120 \text{ Hz}, 12 \text{ V} \le \text{V}_1 \le$	\leq 22 V, T _J = 25°C	38	44		dB
V_D	Dropout Voltage		$T_J = 25^{\circ}C$			1.7		V

- 7. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests. 8. Power dissipation: $P_D \le 0.75 \text{ W}$.

Electrical Characteristics (KA78L10A)

 $V_{I} = 16 \text{ V, } I_{O} = 40 \text{ mA, } -40 \text{ }^{\circ}\text{C} \leq T_{J} \leq 125 \text{ }^{\circ}\text{C, } C_{I} = 0.33 \text{ } \mu\text{F, } C_{O} = 0.1 \text{ } \mu\text{F, unless otherwise specified.}$

Symbol	Paramete	er		Conditions	Min.	Тур.	Max.	Unit		
Vo	Output Voltage		T _J = 25°C		9.6	10.0	10.4	V		
41/	Line Regulation ⁽⁹⁾		T _{.1} = 25°C	12.5 V ≤ V _I ≤ 25 V		100	220	mV		
ΔV_{O}	Line Regulation		1 j = 25 C	14 V ≤ V _I ≤ 25 V		100	170	mV		
41/	Load Regulation ⁽⁹⁾		T _{.1} = 25°C	1 mA ≤ I _O ≤ 100 mA		20	94	mV		
ΔV_{O}	Load Regulation		1 J = 25 C	$1 \text{ mA} \le I_O \le 70 \text{ mA}$		10	47	mV		
			$12.5 \text{ V} \leq \text{V}_{\text{I}} \leq \text{I}$	25 V, 1 mA \leq I _O \leq 40 mA	9.5		10.5			
Vo	Output Voltage		12.5 $V \le V_I \le V_{MAX}^{(10)}$, 1 mA $\le I_O \le 70$ mA		9.5		10.5	V		
	Quiescent Current		$T_J = 25^{\circ}C$				6.0	mA		
IQ	Quiescent Current		T _J =125°C			4.2	6.5	ША		
ΔI_Q	Quiescent Current	With Line	12.5 V ≤ V _I ≤	25 V			1.5	mA		
ΔI_Q	Change	With Load	$1 \text{ mA} \leq I_O \leq 4$	40 mA			0.1	mA		
V _N	Output Noise Voltage	е	$T_A = 25^{\circ}C$, 10 Hz $\leq f \leq$ 100 kHz		$T_A = 25^{\circ}C$, 10 Hz $\leq f \leq$ 100 kHz			74		μV/Vo
$\Delta V_O/\Delta T$	Temperature Coeffic	eient of V _O	I _O = 5 mA			0.95		mV/°C		
RR	Ripple Rejection		$f = 120 \text{ Hz}, 15 \text{ V} \le \text{V}_{\text{I}} \le 25 \text{ V}, \text{T}_{\text{J}} = 25^{\circ}\text{C}$		38	43		dB		
V_D	Dropout Voltage		$T_J = 25^{\circ}C$			1.7		٧		

- 9. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests. 10. Power dissipation: $P_D \le 0.75 \text{ W}$.

Electrical Characteristics (KA78L12A)

 $V_I = 19 \text{ V, I}_O = 40 \text{ mA, -}40^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C, C}_I = 0.33 \text{ }\mu\text{F, C}_O = 0.1 \text{ }\mu\text{F, unless otherwise specified.}$

Symbol	Parame	Parameter		Conditions			Max.	Unit
Vo	Output Voltage		T _J = 25°C		11.5	12.0	12.5	V
$\Delta V_{\mathbf{O}}$	Line Regulation ⁽¹	1)	T _{.I} = 25°C	$14.5 \text{ V} \le \text{V}_{\text{I}} \le 27 \text{ V}$		20	250	mV
7,0	Line Regulation	,	11 = 23 0	16 $V \le V_1 \le 27 V$		15	200	mV
$\Delta V_{\mathbf{O}}$	Load Regulation (11)	$T_J = 25^{\circ}C$	$1~\text{mA} \le I_O \le 100~\text{mA}$		20	100	mV
ΔvO	Load Regulation	,		1 mA \leq I _O \leq 40 mA		10	50	mV
V	Output Voltage		$14.5 \text{ V} \le \text{V}_{\text{I}} \le 27 \text{ V}$	1 mA \leq I _O \leq 40 mA	11.4		12.6	V
Vo	Output voltage		$14.5 \text{ V} \le \text{V}_{\text{I}} \le \text{V}_{\text{MAX}}^{(12)}$	$1~\text{mA} \leq I_O \leq 70~\text{mA}$	11.4		12.6	V
IQ	Quiescent Current	t	$T_J = 25^{\circ}C$			2.1	6.0	mA
ΔI_{Q}	Quiescent	With Line	$16 \text{ V} \leq \text{V}_{\text{I}} \leq 27 \text{ V}$				1.5	mA
ΔI_{Q}	Current Change	With Load	1 mA \leq I _O \leq 40 mA				0.1	mA
V _N	Output Noise Volt	age	$T_A = 25^{\circ}C, 10 \text{ Hz} \le f \le$	100 kHz		80		μV/Vo
$\Delta V_O/\Delta T$	Temperature Coefficient of V _O		$I_O = 5 \text{ mA}$			-1.0		mV/°C
RR	Ripple Rejection		f = 120 Hz, 15 V ≤ V _I ≤	25 V, T _J = 25°C	37	65		dB
V_D	Dropout Voltage		T _J = 25°C			1.7	70.	V

- 11. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests. 12. Power dissipation: $P_D \le 0.75 \text{ W}$.

Electrical Characteristics (KA78L15A)

 $V_I = 23~V,~I_O = 40~mA,~-40^{\circ}C \leq T_J \leq 125^{\circ}C,~C_I = 0.33~\mu F,~C_O = 0.1~\mu F,~unless~otherwise~specified.$

Symbol	Parame	eter	Condit	ions	Min.	Тур.	Max.	Unit
Vo	Output Voltage		T _J = 25°C		14.4	15.0	15.6	V
$\Delta V_{\mathbf{O}}$	Line Regulation ⁽¹	13)	T _{.1} = 25°C	17.5 V ≤ V _I ≤ 30 V		25	300	mV
ΔvO	Line Regulation	,	1j = 25 C	20 V ≤ V _I ≤ 30 V		20	250	mV
41/	Load Regulation	(13)	T _{.1} = 25°C	$1 \text{ mA} \le I_{O} \le 100 \text{ mA}$		25	150	mV
ΔV_{O}	Load Regulation	,	1 _J = 25 C	$1 \text{ mA} \le I_O \le 40 \text{ mA}$		12	75	mV
\/	Output Voltage		$17.5 \text{ V} \le \text{V}_{\text{I}} \le 30 \text{ V}$	$1 \text{ mA} \le I_O \le 40 \text{ mA}$	14.25		15.75	V
Vo	Output voltage		$17.5 \text{ V} \le \text{V}_{\text{I}} \le \text{V}_{\text{MAX}}^{(14)}$	$1~\text{mA} \leq I_O \leq 70~\text{mA}$	14.25		15.75	V
IQ	Quiescent Curre	nt	$T_J = 25^{\circ}C$			2.1	6.0	mA
ΔI_{Q}	Quiescent	With Line	$20~V \leq V_I \leq 30~V$				1.5	mA
ΔI_{Q}	Current Change	With Load	1 mA \leq I _O \leq 40 mA				0.1	mA
V _N	Output Noise Vo	ltage	$T_A = 25^{\circ}C, 10 \text{ Hz} \le f \le$	100 kHz		90		μV/Vo
$\Delta V_{O}/\Delta T$	Temperature Coefficient of V _O		I _O = 5 mA			-1.3		mV/°C
RR	Ripple Rejection		$f = 120 \text{ Hz}, 18.5 \text{ V} \le \text{V}$	I ≤ 28.5 V, T _J =25°C	34	60		dB
V _D	Dropout Voltage	_	T _J = 25°C			1.7		V

- 13. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests. 14. Power dissipation: $P_D \le 0.75 \text{ W}$.

Electrical Characteristics (KA78L18A)

 $V_I = 27 \text{V, I}_O = 40 \text{mA, -} 40^\circ \text{C} \leq T_J \leq 125^\circ \text{C, C}_I = 0.33 \, \mu\text{F, C}_O = 0.1 \, \mu\text{F, unless otherwise specified.}$

Symbol	Parame	Parameter		Conditions		Тур.	Max.	Unit
Vo	Output Voltage		T _J = 25°C		17.3	18.0	18.7	V
$\Delta V_{\mathbf{O}}$	Line Regulation (1	5)	T _{.1} = 25°C	$21~V \leq V_I \leq 33~V$		145	300	mV
ΔνΟ	Line Regulation	,	11 - 23 0	$22~V \leq V_I \leq 33~V$		135	250	mV
41/	Load Regulation (15)	T _{.1} = 25°C	1 mA ≤ I _O ≤100 mA		30	170	mV
ΔV_{O}	Load Regulation		1j = 25 C	1 mA \leq I _O \leq 40 mA		15	85	mV
W	Output Voltage		$21~V \leq V_I \leq 33~V$	1 mA \leq I _O \leq 40 mA	17.1		18.9	V
Vo	Output voltage		$21V \le V_I \le V_{MAX}^{(16)}$	1 mA \leq I _O \leq 70 mA	17.1		18.9	V
IQ	Quiescent Curren	t	T _J = 25°C			2.2	6.0	mA
ΔI_{Q}	Quiescent	With Line	$21~V \leq V_I \leq 33~V$				1.5	mA
ΔI_{Q}	Current Change	With Load	1 mA \leq I _O \leq 40 mA				0.1	mA
V _N	Output Noise Volt	age	$T_A = 25^{\circ}C$, 10 Hz \leq f	≤ 100 kHz		150		μV/Vo
$\Delta V_O/\Delta T$	Temperature Coefficient of V _O		$I_O = 5 \text{ mA}$			-1.8		mV/°C
RR	Ripple Rejection		f = 120 Hz, 23 V ≤ V	_I ≤ 33V, T _J = 25°C	34	48		dB
V_D	Dropout Voltage		T _J = 25°C			1.7		V

- 15. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.

 16. Power dissipation: $P_D \le 0.75 \text{ W}$.

Electrical Characteristics (KA78L05AA)

 $V_I = 10 \text{ V, } I_O = 40 \text{ mA, } 0^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C, } C_I = 0.33 \text{ } \mu\text{F, } C_O = 0.1 \text{ } \mu\text{F, unless otherwise specified.}$

Symbol	Parameter		Cond	Conditions		Тур.	Max.	Unit
Vo	Output Voltage		T _J = 25°C		4.9	5.0	5.1	V
۸\/	Line Regulation (17)	1	T _{.1} = 25°C	7 V ≤ V _I ≤ 20 V		8	150	mV
ΔV_{O}	Line Regulation .		1 j = 25 C	8 V ≤ V _I ≤ 20 V		6	100	mV
41/	Load Regulation (17	')	T _{.1} = 25°C	1 mA ≤ I _O ≤ 100 mA		11	50	mV
ΔV_{O}	Load Regulation	,	1 J = 25 C	1 mA \leq I _O \leq 40 mA		5.0	25	mV
W	Output Voltage		7 V ≤V _I ≤ 20 V	1 mA \leq I _O \leq 40 mA			5.15	V
V _O	Output Voltage		$7 \text{ V} \leq \text{V}_{\text{I}} \leq \text{V}_{\text{MAX}}^{(18)}$	1 mA \leq I _O \leq 70 mA	4.85		5.15	V
IQ	Quiescent Current		T _J = 25°C			2.0	5.5	mA
ΔI_{Q}	Quiescent Current	With Line	8 V ≤V _I ≤ 20 V				1.5	mA
ΔI_{Q}	Change	With Load	1 mA \leq I _O \leq 40 mA				0.1	mA
V _N	Output Noise Voltag	ge	T _A = 25°C, 10 Hz ≤	≤ f ≤ 100 kHz		40		μV/Vo
$\Delta V_O/\Delta T$	Temperature Coefficient of V _O		I _O = 5 mA			-0.65		mV/°C
RR	Ripple Rejection		f = 120 Hz, 8 V ≤ V	$I_{\rm I} \le 18 \rm V, T_{\rm J} = 25^{\circ} \rm C$	41	80		dB
V_{D}	Dropout Voltage		T _J = 25°C			1.7	7	V

- 17. The maximum steady-state usable output current and input voltage are very dependent on the heat sinking and/or lead length of the package. The data above represents pulse test conditions with junction temperature as indicated at the initiation of tests.

 18. Power dissipation: $P_D \le 0.75 \text{ W}$.

Typical Application

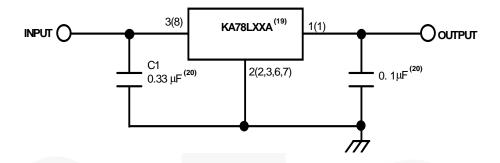


Figure 2. Typical Application

- 19. To specify an output voltage, substitute voltage value for "XX".
- 20. Bypass capacitors are recommend for optimum stability and transient response and should be located as close as possible to the regulator.

Physical Dimensions 4.70 4.30 2.23 MIN 1.87 1.45 0.50 X 45° 0.30 X 45° В (1.40) € SYMM 2.70 5.30 MIN 4.50 3.90⁴ 2.30 1.30 0.89 0.52 0.30 (2X) C 0.10 M C A B (0.54) 1.50 3.00 0.90 MIN 2X 0.96 MIN 1.70 1.30 1.50 3.00 MIN LAND PATTERN RECOMMENDATION SEATING PLANE 0.60 <u>C</u> 0.40 0.50 0.35 (0.35) 2.29 (2.70) 2.13 NOTES: UNLESS OTHERWISE SPECIFIED. A. REFERENCE TO JEDEC TO-243 VARIATION AA. B. ALL DIMENSIONS ARE IN MILLIMETERS. DOES NOT COMPLY JEDEC STANDARD VALUE. D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSION. E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994. F. DRAWING FILE NAME: MA03CREV3

Figure 3. 3-LEAD, SOT-89, JEDEC TO-243, OPTION AA

Physical Dimensions (Continued)

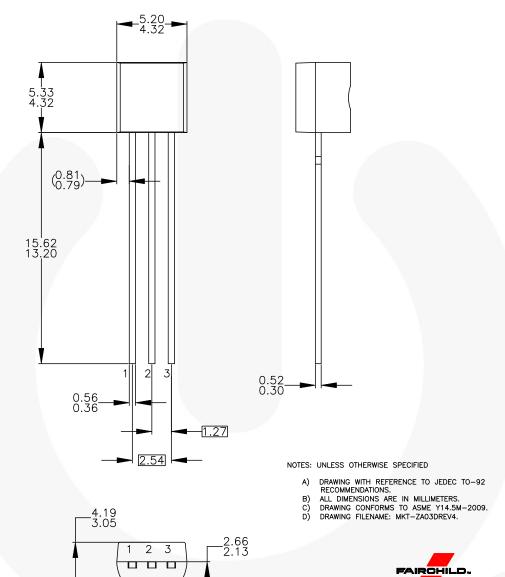
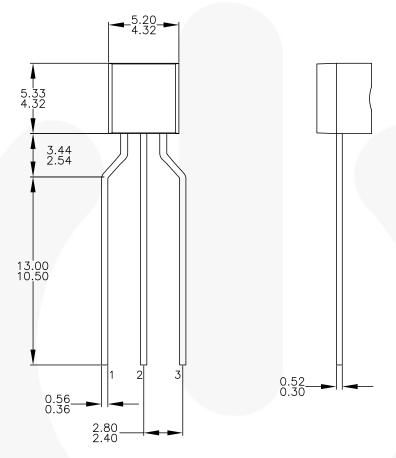
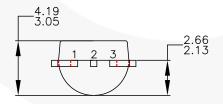


Figure 4. 3-LEAD, TO-92, JEDEC TO-92 COMPLIANT STRAIGHT LEAD CONFIGURATION, BULK TYPE

Physical Dimensions (Continued)





NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC. ALL DIMENSIONS ARE IN MILLIMETERS. DRAWING CONFORMS TO ASME Y14.5M-2009. DRAWING FILENAME: MKT-ZAO3FREV3. FAIRCHILD SEMICONDUCTOR.

Figure 5. 3-LEAD, TO-92, MOLDED 0.200 IN LINE SPACING LEAD FORM, AMMO TYPE

Physical Dimensions (Continued) **→** A 4.90±0.10-0.65 (0.635)В 1.75 6.00±0.20 5.60 3.90±0.10 PIN ONE INDICATOR 1.27 1.27 0.25 \bigcirc C B A LAND PATTERN RECOMMENDATION SEE DETAIL A 0.175±0.075 0.22±0.03 1.75 MAX \bigcirc 0.10 0.42±0.09 OPTION A - BEVEL EDGE $-(0.86) \times 45^{\circ}$ R0.10 **GAGE PLANE** OPTION B - NO BEVEL EDGE R0.10 0.36 NOTES: A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA. SEATING PLANE B) ALL DIMENSIONS ARE IN MILLIMETERS. 0.65±0.25 C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS. (1.04)D) LANDPATTERN STANDARD: SOIC127P600X175-8M **DETAIL A** E) DRAWING FILENAME: M08Arev16

Figure 6. 8-LEAD, SOIC, JEDEC MS-012, 0.150" NARROW BODY





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